

Tianshi Liu

List of Publications by Year in descending order

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15
papers

126
citations

1937685

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2272923

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all docs

15
docs citations

15
times ranked

45
citing authors

#	ARTICLE	IF	CITATIONS
1	Time-Dependent Dielectric Breakdown of Commercial 1.2 kV 4H-SiC Power MOSFETs. IEEE Journal of the Electron Devices Society, 2021, 9, 633-639.	2.1	30
2	Monolithic Integration of Lateral HV Power MOSFET with LV CMOS for SiC Power IC Technology. , 2021, , .		15
3	Gate Leakage Current and Time-Dependent Dielectric Breakdown Measurements of Commercial 1.2 kV 4H-SiC Power MOSFETs. , 2019, , .		14
4	Gate Oxide Reliability Studies of Commercial 1.2 kV 4H-SiC Power MOSFETs. , 2020, , .		12
5	Investigation of Gate Leakage Current Behavior for Commercial 1.2 kV 4H-SiC Power MOSFETs. , 2021, , .		11
6	The Road to a Robust and Affordable SiC Power MOSFET Technology. Energies, 2021, 14, 8283.	3.1	10
7	Threshold Voltage Instability of Commercial 1.2 kV SiC Power MOSFETs. , 2020, , .		8
8	Design Strategies for Rugged SiC Power Devices. , 2019, , .		6
9	Comparison of Gate Oxide Lifetime Predictions with Charge-to-Breakdown Approach and Constant-Voltage TDDB on SiC Power MOSFET. , 2021, , .		6
10	SPICE Modeling and Circuit Demonstration of a SiC Power IC Technology. IEEE Journal of the Electron Devices Society, 2022, 10, 129-138.	2.1	4
11	JFET Region Design Trade-Offs of 650 V 4H-SiC Planar Power MOSFETs. Solid State Electronics Letters, 2021, 3, 53-58.	1.0	4
12	SPICE Modeling and CMOS Circuit Development of a SiC Power IC Technology. , 2021, , .		2
13	3.3-kV SiC MOSFET Performance and Short-Circuit Capability. , 2020, , .		2
14	Impacts of Area-Dependent Defects on the Yield and Gate Oxide Reliability of SiC Power MOSFETs. , 2021, , .		1
15	Bias Temperature Instability on SiC n- and p-MOSFETs for High Temperature CMOS Applications. , 2022, , .		1